SSC8035GSB

P-Channel Enhancement Mode MOSFET

- **Features**

VDS	VGS	RDSon TYP	ID
-30V	±12V	51mR@-10V	-4.2A
		60mR@-4V5	
		98mR@-2V5	

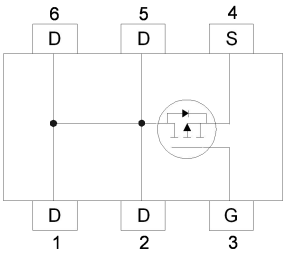
- **General Description**

This device is particularly suited for low voltage application such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package Excellent thermal and electrical capabilities.

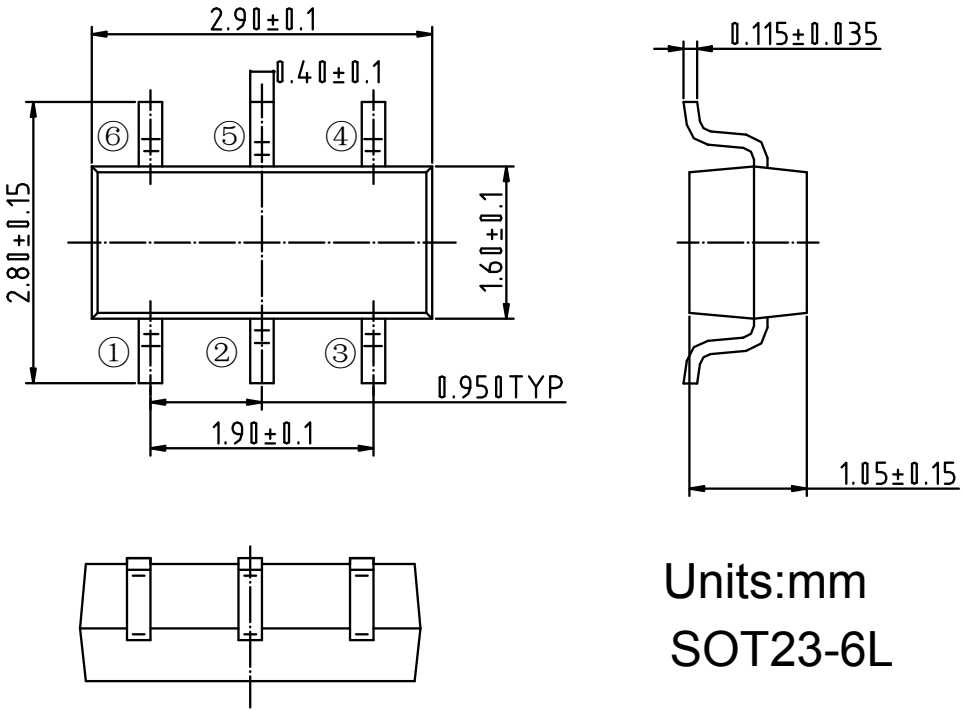
- **Applications**
  - Load Switch
  - Portable Devices
  - DCDC conversion

- **Pin configuration**

Top View



- **Package Information**



Units:mm

SOT23-6L

- **Absolute Maximum Ratings** @T_A=25℃ unless otherwise noted

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	±12	V
Maximum Drain Current – Continuous – Pulsed	I_D I_{DM}	-4.2 -30	A
Continuous Power Dissipation	P_D	1000	mW
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	℃

- **Electrical Characteristics** @T_A=25℃ unless otherwise noted

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μ A	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30V, V_{GS} =0V	--	--	-1	μA
Gate - Body Leakage, Forward	I_{GSSF}	V_{GS} = -12V	--	--	-100	nA
Gate - Body Leakage, Reverse	I_{GSSR}	V_{GS} =12V	--	--	100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS\ (TH)}$	V_{DS} = V_{GS}, I_D = -250μA	-0.7	-1.0	-1.3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS} = -10V, I_D = -4.2A	--	51	65	mR
		V_{GS} = -4.5V, I_D = -4A	--	60	75	
		V_{GS} = -2.5V, I_D = -1A	--	98	120	
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{DS} = -30V, V_{GS} = 0V, F = 200KHz	--	600	--	pF
Output Capacitance	C_{OSS}		--	85	--	pF
Reverse Transfer Capacitance	C_{RSS}		--	66	--	pF
SWITCHING CHARACTERISTICS						
Turn-on Delay Time	$T_{D\ (ON)}$	V_{GS}=-10V, V_{DS}=-15V, R_L=3.6R,R_{GEN}=6R	--	6.5	--	ns
Rise Time	T_R		--	3.5	--	
Turn-off Delay Time	$T_{D(OFF)}$		--	40	--	
Fall Time	T_F		--	13	--	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = -1A	--	-0.78	-1	V

Note:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

- **Typical Performance Characteristics**

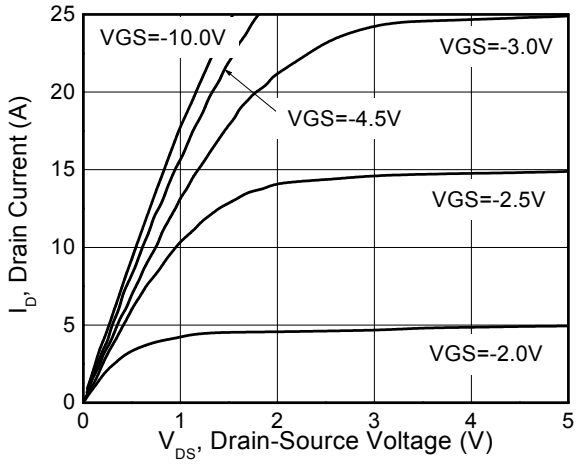


Figure 1. Output Characteristics

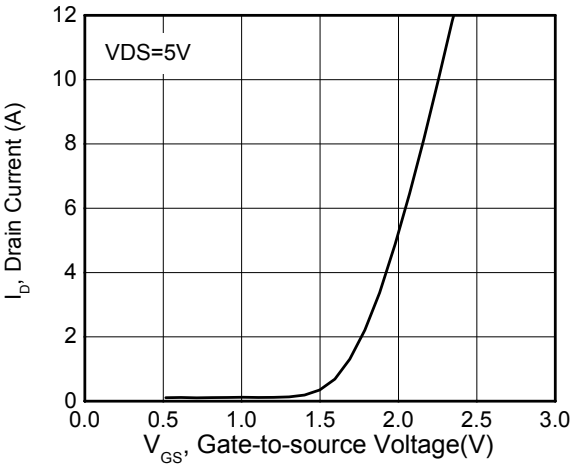


Figure 2. Transfer Characteristics

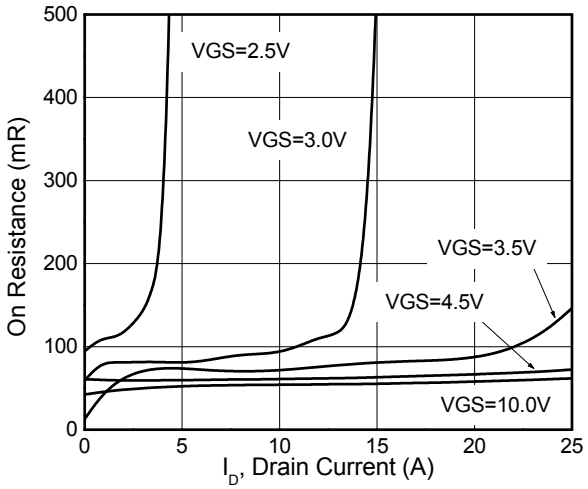


Figure 3. On-Resistance vs. Drain Current

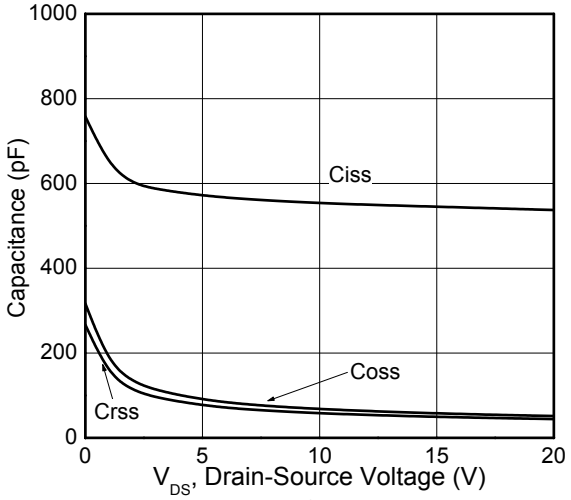


Figure 4. Capacitance

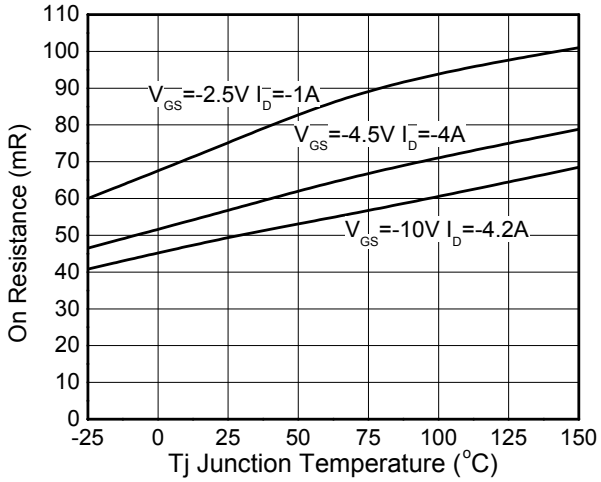


Figure 5 . On-Resistance vs. Temperature

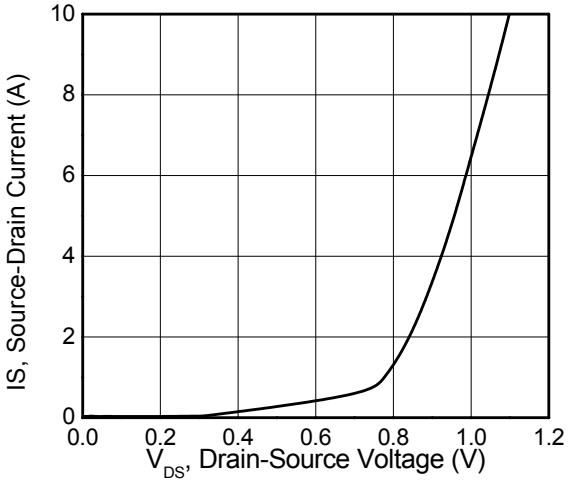


Figure 6. Diode Forward Characteristics

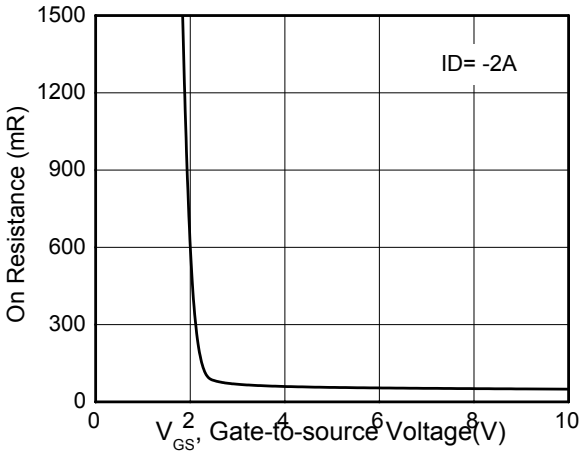


Figure 7. On Resistance vs. G-S Voltage

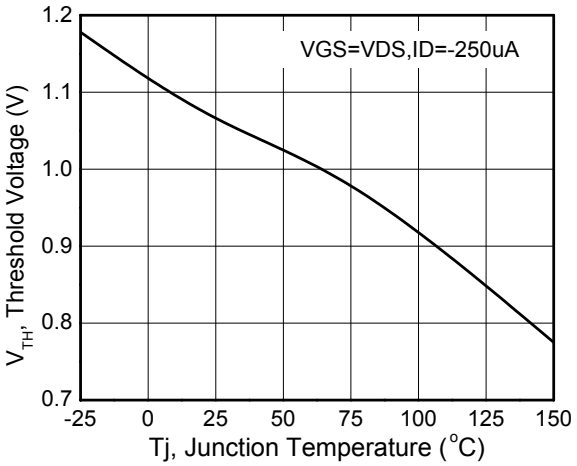


Figure 8. Threshold vs. Temperature

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